

P-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 150	1.2 at $V_{GS} = - 10$ V	- 0.69	7.7
	1.3 at $V_{GS} = - 6.0$ V	- 0.66	

FEATURES

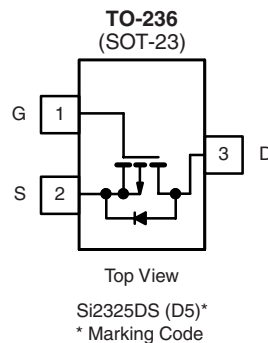
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- Ultra Low On-Resistance
- Small Size



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Active Clamp Circuits in DC/DC Power Supplies



Ordering Information: Si2325DS -T1-E3 (Lead (Pb)-free)
Si2325DS -T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 150		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	- 0.69	- 0.53	A
		- 0.55	- 0.43	
Pulsed Drain Current	I_{DM}	- 1.6		
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	- 1.0	- 0.6	
Single Pulse Avalanche Current	I_{AS}	4.5		mJ
Single Pulse Avalanche Energy	E_{AS}	1.01		
Maximum Power Dissipation ^{a, b}	P_D	1.25	0.75	W
		0.8	0.48	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	75	100	°C/W
		120	166	
Maximum Junction-to-Foot (Drain)	R_{thJF}	40	50	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 250 μA	- 150			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 2.5		- 4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 150 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 150 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 15 V, V _{GS} = 10 V	- 1.6			A
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 0.5 A		1.0	1.2	Ω
		V _{GS} = - 6.0 V, I _D = - 0.5 A		1.05	1.3	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 0.5 A		2.2		S
Diode Forward Voltage	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		0.7	- 1.2	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = - 75 V, V _{GS} = 10 V, I _D ≅ - 0.5 A		7.7	12	nC
Gate-Source Charge	Q _{gs}			1.5		
Gate-Drain Charge	Q _{gd}			2.5		
Gate Resistance	R _g	f = 1.0 MHz		9		Ω
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		340	510	pF
Output Capacitance	C _{oss}			30		
Reverse Transfer Capacitance	C _{rss}			16		
Switching ^c						
Turn-On Time	t _{d(on)}	V _{DD} = - 75 V, R _L = 75 Ω I _D ≅ - 1.0 A, V _{GEN} = - 10 V R _g = 6 Ω		7	11	ns
	t _r			11	17	
Turn-Off Time	t _{d(off)}			16	25	
	t _f			11	17	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 0.5 A, dI/dt = 100 A/μs		90	135	nC

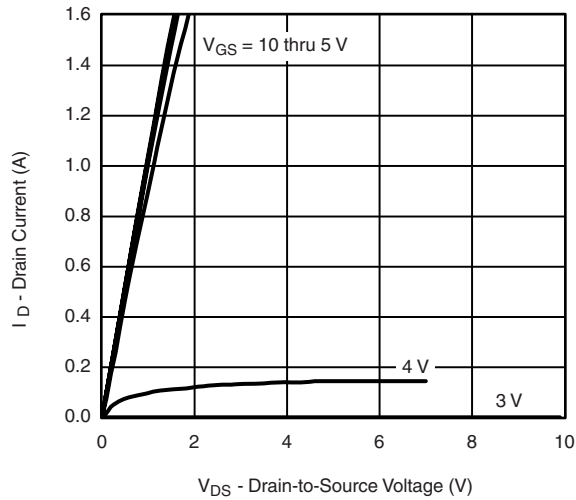
Notes:

- a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
b. For DESIGN AID ONLY, not subject to production testing.
c. Switching time is essentially independent of operating temperature.

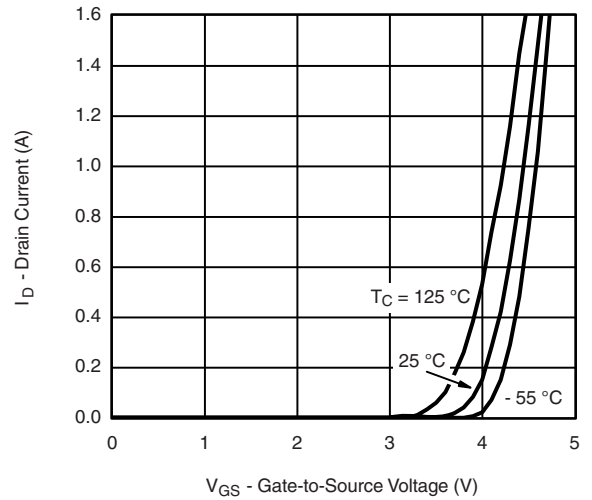
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



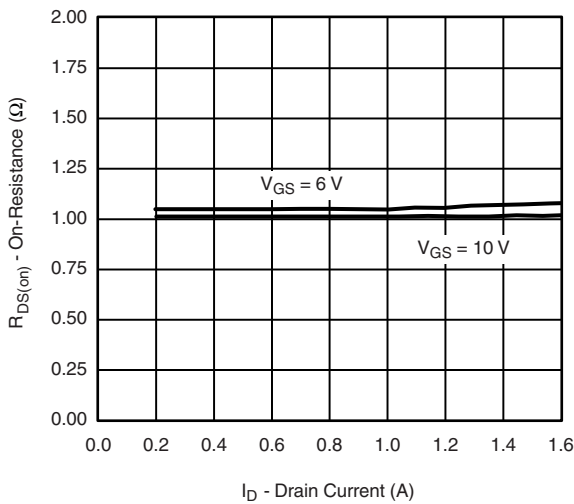
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



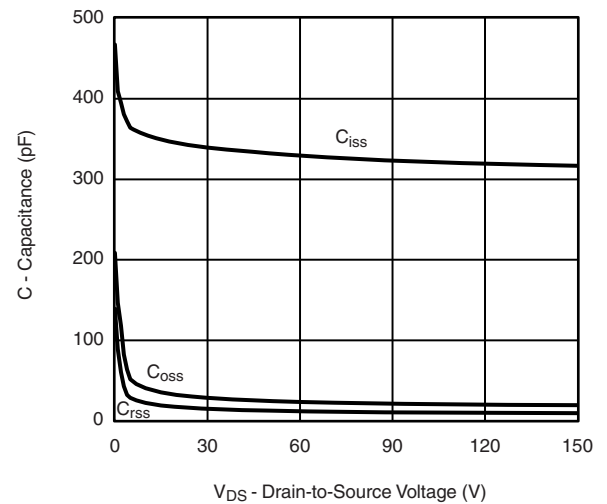
Output Characteristics



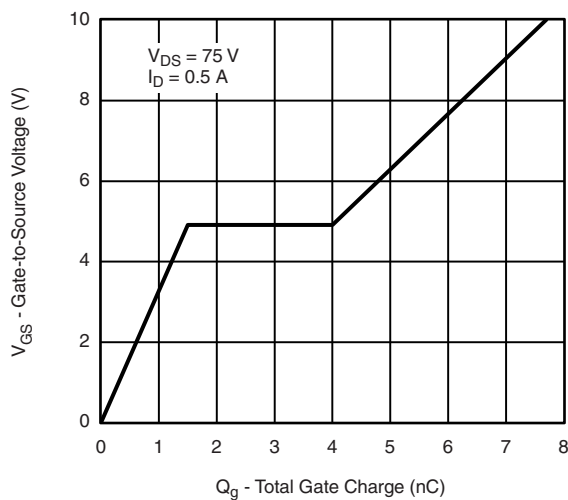
Transfer Characteristics



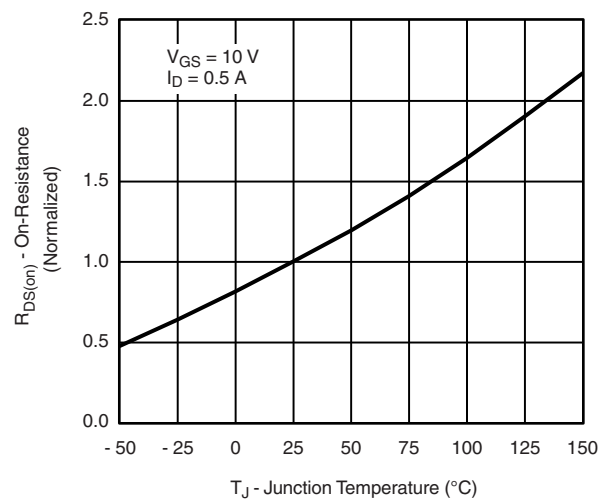
On-Resistance vs. Drain Current



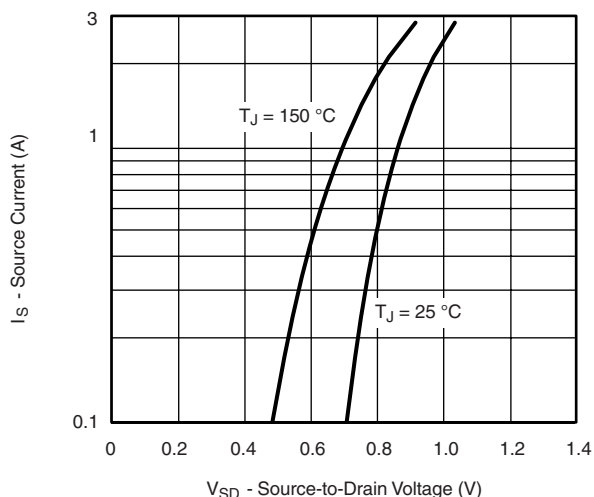
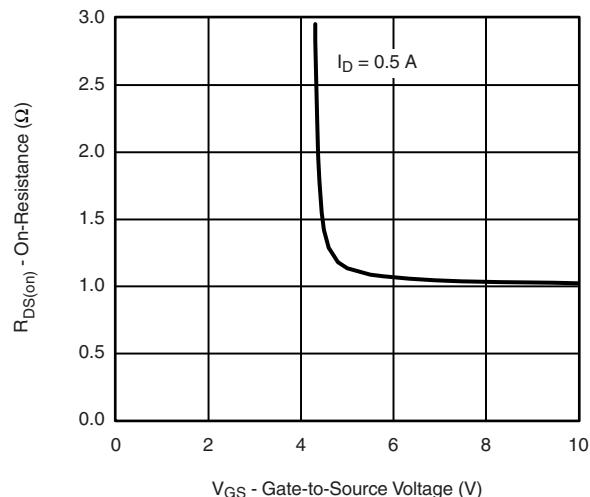
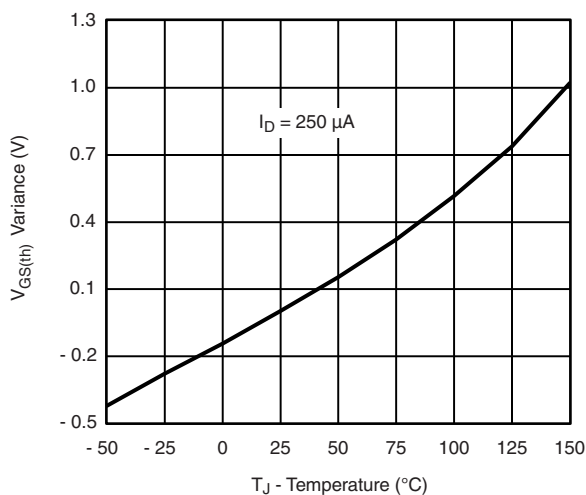
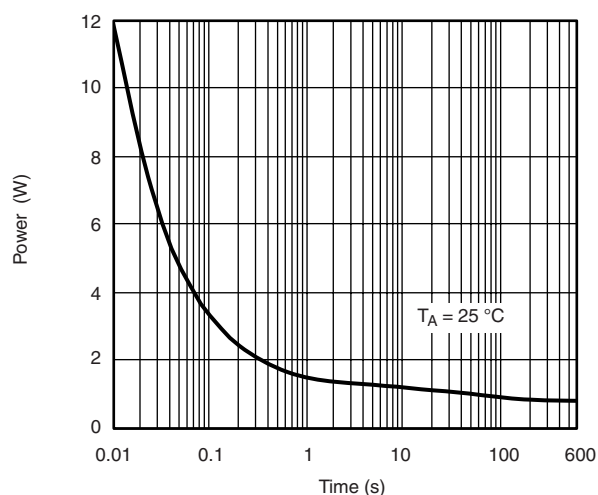
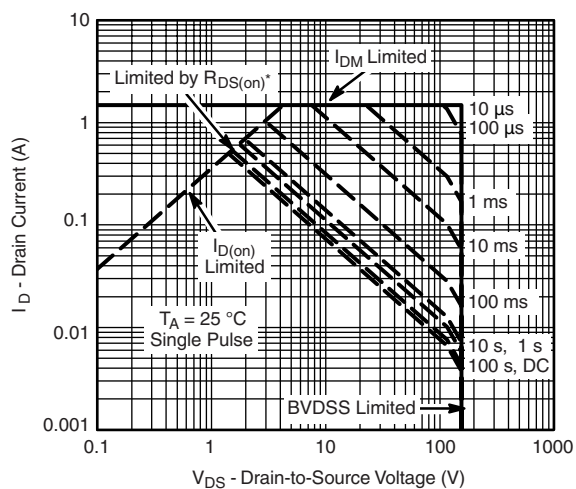
Capacitance



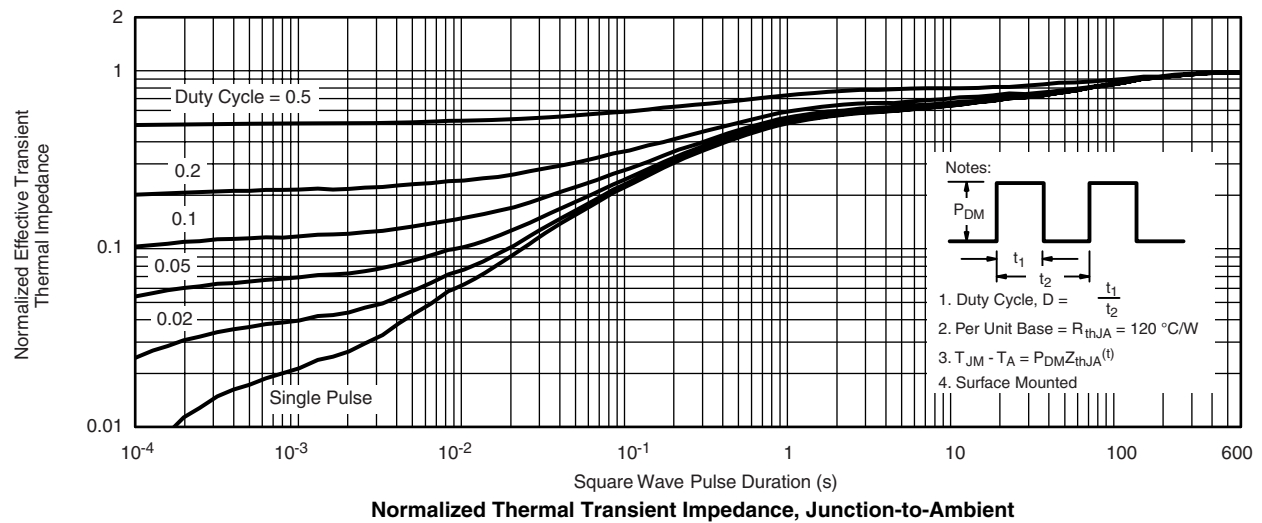
Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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